

advanced

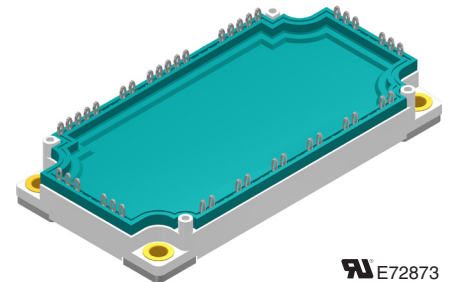
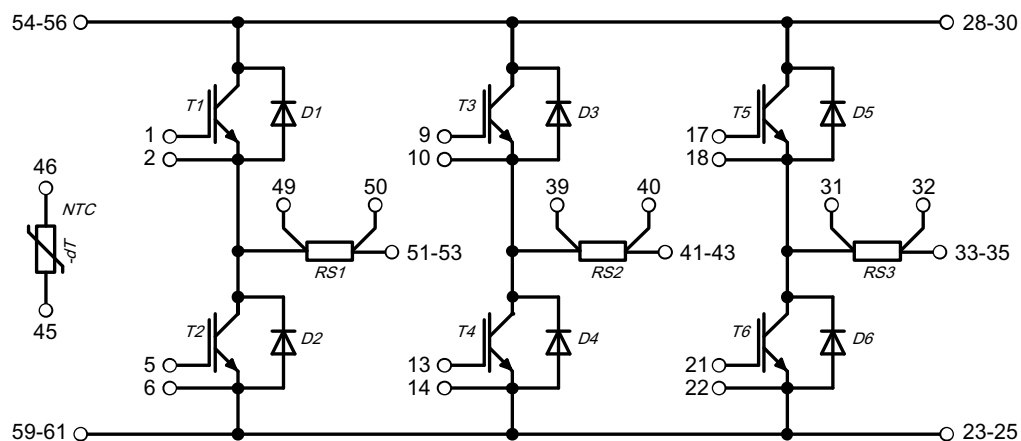
$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 312 \text{ A} \\ V_{CE(sat)} &= 1.7 \text{ V} \end{aligned}$$

X2PT IGBT Module

6-Pack + NTC + Shunt

Part number

MIXG240W1200PZTEH


 E72873


Features / Advantages:

- X2PT - 2nd generation Xtreme light Punch Through
- $T_{VJm} = 175^{\circ}\text{C}$
- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged X2PT design results in:
 - short circuit rated for 10 μs c.
 - very low gate charge
 - low EMI
 - square RBSOA @ $2 \times I_c$
- Low $V_{CE(sat)}$ and low thermal resistance
- SONIC2™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package: E3-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- PressFit pins

Option:

- Phase Change Material printed on base plate

Disclaimer Notice

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Inverter IGBT T1 - T6				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V_{CES}	collector emitter voltage	$I_R = 500 \mu A$	$T_{VJ} = 25^\circ C$	1200			V
V_{GES}	max. DC gate voltage			-20		+20	V
V_{GEM}	max. transient gate emitter voltage			-30		+30	V
I_{C25}	collector current		$T_C = 25^\circ C$			312	A
I_{C80}			$T_C = 80^\circ C$			233	A
I_{C100}			$T_C = 100^\circ C$			200	A
P_{tot}	total power dissipation		$T_C = 25^\circ C$			938	W
$V_{CE(sat)}$	collector emitter saturation voltage on die level	$I_C = 200 A; V_{GE} = 15 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.7 2	2	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 8 mA; V_{GE} = V_{GE}$	$T_{VJ} = 25^\circ C$	6.0		7.5	V
I_{CES}	collector emitter leakage current (includes diode reverse current)	$V_{CE} = V_{CES}; V_{GE} = 0 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		2	0.15	mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20 V$				500	nA
R_G	internal gate resistance				6.5		Ω
C_{iss}	input capacitance	$V_{CE} = 100 V; V_{GS} = 0 V; f = 1 MHz$			10.6		nF pF pF
C_{oss}	output capacitance						
C_{rss}	reverse transfer (Miller) capacitance						
Q_g	total gate charge	$V_{CE} = 600 V; V_{GE} = 0 / 15 V; I_C = 200 A$			630		nC nC nC
Q_{gs}	gate source charge						
Q_{gd}	gate drain (Miller) charge						
$t_{d(on)}$	turn-on delay time	Inductive switching $V_{CE} = 680 V; I_C = 200 A$ $V_{GE} = \pm 15 V; R_G = 3.9 \Omega$ (external) $T_{VJ} = 25^\circ C$			170 55 290 120 17.1 14.2 4.6		ns ns ns ns mJ mJ mJ
t_r	current rise time						
$t_{d(off)}$	turn-off delay time						
t_f	current fall time						
E_{on}	turn-on energy per pulse						
E_{off}	turn-off energy per pulse						
$E_{rec(off)}$	reverse recovery losses at turn-off						
$t_{d(on)}$	turn-on delay time	Inductive switching $V_{CE} = 680 V; I_C = 200 A$ $V_{GE} = \pm 15 V; R_G = 3.9 \Omega$ (external) $T_{VJ} = 150^\circ C$			180 70 360 215 23.5 20.5 12.2		ns ns ns ns mJ mJ mJ
t_r	current rise time						
$t_{d(off)}$	turn-off delay time						
t_f	current fall time						
E_{on}	turn-on energy per pulse						
E_{off}	turn-off energy per pulse						
$E_{rec(off)}$	reverse recovery losses at turn-off						
$RBSOA$	reverse bias safe operating area	$V_{GE} = \pm 15 V; R_G = 3.9 \Omega$	$T_{VJ} = 150^\circ C$			400	A
I_{CM}		$V_{CEmax} = 1200 V$					
$SCSOA$	short circuit safe operating area	$V_{CEmax} = 1200 V$	$T_{VJ} = 150^\circ C$		900	10	μs A
t_{SC}	short circuit duration	$V_{CE} = 900 V; V_{GE} = \pm 15 V$					
I_{SC}	short circuit current	non-repetitive					
R_{thJC}	thermal resistance junction to case	with heatsink compound; IXYS test setup			0.24	0.16	K/W
R_{thJH}	thermal resistance junction to heatsink						K/W

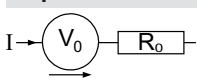
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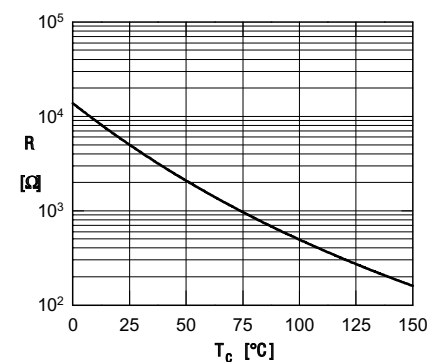
Inverter Diode D1 - D6				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage	$I_R = 500 \mu A$, see V_{CES}	$T_{VJ} = 25^\circ C$	1200			V
I_{F25} I_{F80} I_{F100}	forward current		$T_C = 25^\circ C$ $T_C = 80^\circ C$ $T_C = 100^\circ C$			189 136 114	A A A
V_F	forward voltage on die level	$I_F = 200 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.87 1.85	2.2 2,2	V V
I_R	reverse current * not applicable, see I_{ces} at IGBT	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		*	*	mA mA
Q_{RM} I_{RM} t_{rr} di/dt E_{rec}	reverse recovery charge max. reverse recovery current reverse recovery time rate of change of current reverse recovery energy	$V_{CE} = 600 V$; $I_C = 200 A$ $V_{GE} = \pm 15 V$; $R_G = 3.9 \Omega$ (external)	$T_{VJ} = 25^\circ C$		12 170 240 4200 4.6		μC A ns A/ μs mJ
Q_{RM} I_{RM} t_{rr} di/dt E_{rec}	reverse recovery charge max. reverse recovery current reverse recovery time rate of change of current reverse recovery energy		$T_{VJ} = 150^\circ C$		26 195 480 3600 12.2		μC A ns A/ μs mJ
R_{thJC} R_{thJH}	thermal resistance junction to case thermal resistance junction to heatsink	with heatsink compound; IXYS test setup			0.48	0.38	K/W K/W

Shunt Resistor				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	Unit
R_{SHUNT}	resistance temperature coefficient		$T_C = 25^\circ C$	0.495	0.500	0.505 50	m Ω ppm/K
R_{thSH}	thermal resistance shunt to heatsink	with heatsink compound; IXYS test setup *			10		K/W

* Note: Continous shunt temperature should not exceed 170°C

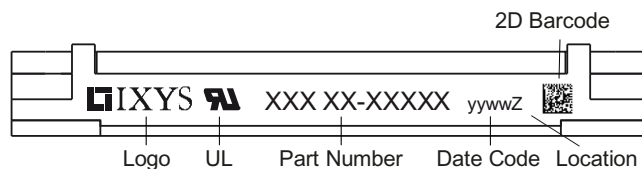
Temperature Sensor NTC						
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ C$	4.75	5.0	5.25	k Ω
$B_{25/50}$	temperature coefficient			3375		K

Equivalent Circuits for Simulation				* on die level	
			IGBT	Boost Diode	
$V_{0 max}$	threshold voltage	$T_{VJ} = 125^\circ C$			V
$R_{0 max}$	slope resistance *				m Ω
$V_{0 max}$	threshold voltage	$T_{VJ} = 175^\circ C$	1.2	1.2	V
$R_{0 max}$	slope resistance *		5.8	4.7	m Ω



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Package E3-Pack				Ratings		Unit
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{RMS}	RMS current	per terminal			30	A
T_{stg}	storage temperature		-40		125	°C
T_{op}	operation temperature		-40		150	°C
T_{VJ}	virtual junction temperature		-40		175	°C
Weight				320		g
M_D	mounting torque		3		6	Nm
d_{Spp}	creepage distance on surface	terminal to terminal	6.0			mm
d_{Spb}		terminal to backside	12.0			mm
d_{App}	striking distance through air	terminal to terminal	6.0			mm
d_{Apb}		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute	4300 3600			V V
$R_{pin-chip}$	resistance pin to chip	$V = V_{CEsat} + 2 \cdot R \cdot I_C$ resp. $V = V_F + 2 \cdot R \cdot I_F$				mΩ
C_P	coupling capacity per switch	between shorted pins of switch and back side metallization				pF

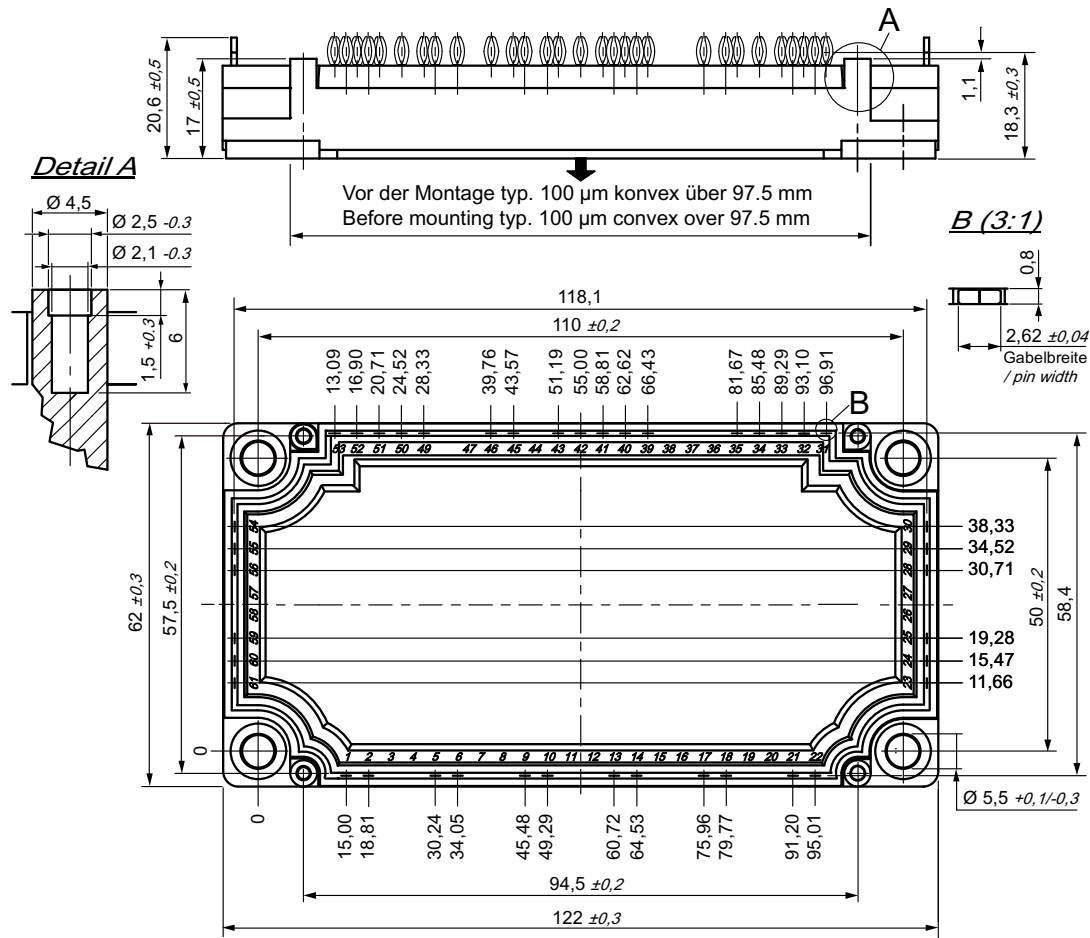

Part number

M = Module
 I = IGBT
 X = XPT IGBT
 G = Gen 2 / std
 240 = Current Rating [A]
 W = 6-pack
 1200 = Reverse Voltage [V]
 PZT = PressFit Pin + Shunt 0.5mΩ, Thermistor
 EH = E3-Pack

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXG240W1200PZTEH	MIXG240W1200PZTEH	Blister	24	MIXG240W1200PZTEH
with Phase Change Material	MIXG240W1200PZTEH -PC ¹⁾	MIXG240W1200PZTEH	Blister	24	

Similar Part	Package	Voltage class
MIXG240W1200TEH	E3- Pack	1200
MIXG240W1200PTEH ²⁾	E3- Pack, press fit pin	1200

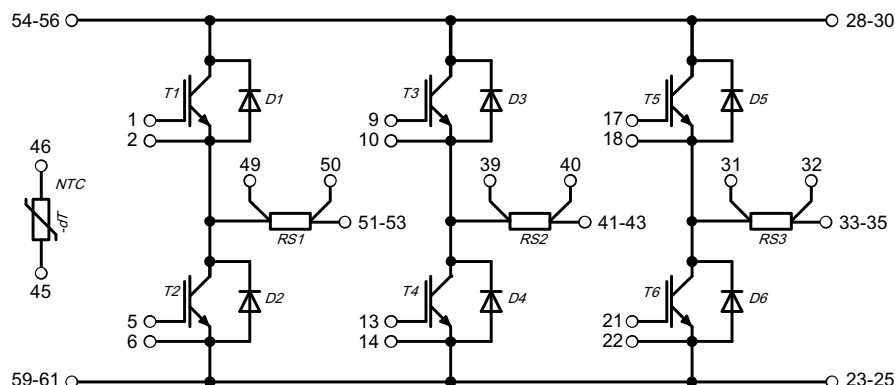
Options: ¹⁾ phase change material and ²⁾ press fit pin
 Please contact Littelfuse - IXYS sales office for availability

Outlines E3-Pack

Bemerkung / Note:

- Nichttolerierete Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern: $\oplus 0.1$
- Bohrlochdurchmesser / Diameter of drill: **Ø 2.35 mm**
- Endlochdurchmesser / Diameter of plated holes: **Ø 2.14 - 2.29 mm** (Cu thickness in via typ. 50 µm)
- Beschichtung / Plating: **chem. Sn max. 15 µm**
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of 7 mm/s: **typ. 90 N**
- Weitere Angaben / Further information: www.ixys.com **Application note IXAN0077**
- Montageanleitung / Mounting instruction: www.ixys.com **Application note IXAN0024**

Detail A: PCB-Montage / Mounting on PCB

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



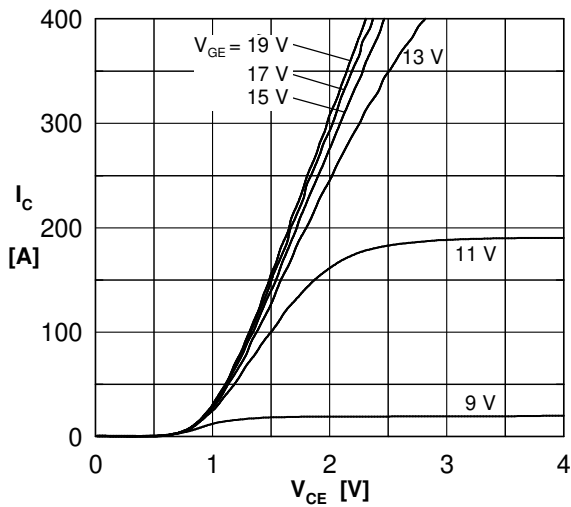
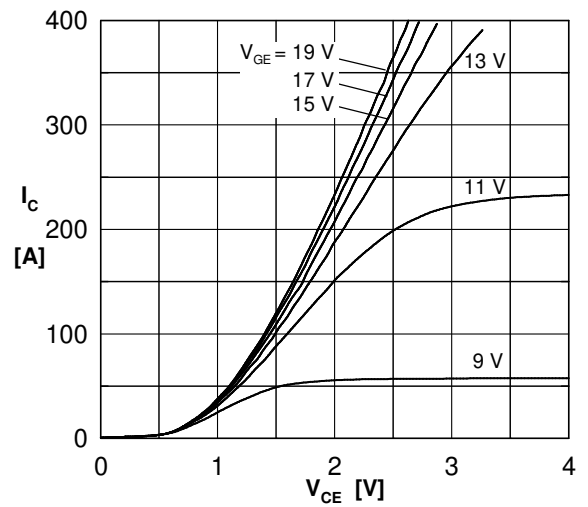
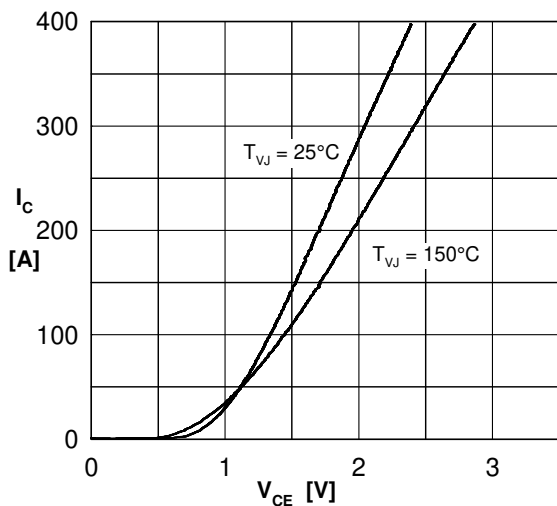
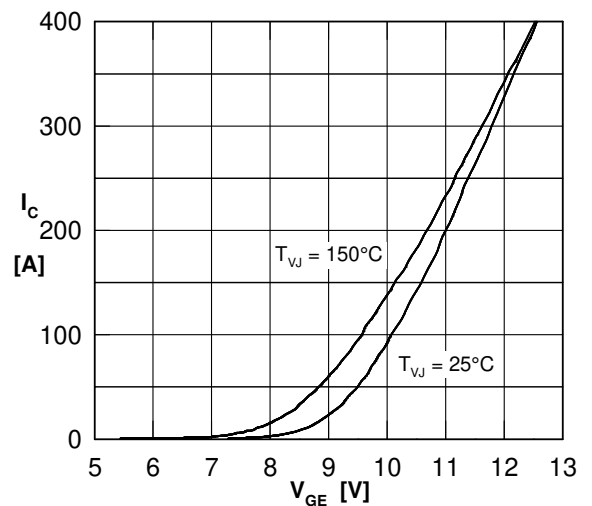
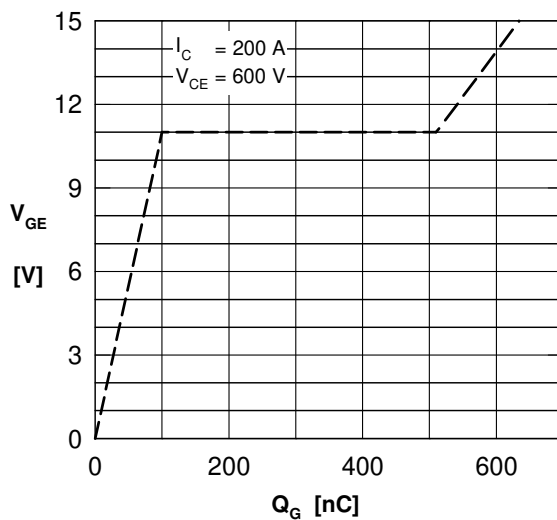
IGBT T1 - T6

 Fig. 1 Typ. output characteristics ($T_{VJ} = 25^\circ\text{C}$)

 Fig. 2 Typ. output characteristics ($T_{VJ} = 150^\circ\text{C}$)

 Fig. 3 Typ. output characteristics ($V_{GE} = 15\text{ V}$)

 Fig. 4 Typ. transfer characteristics ($V_{CE} = 20\text{ V}$)


Fig. 5 Typ. turn-on gate charge 0/15V

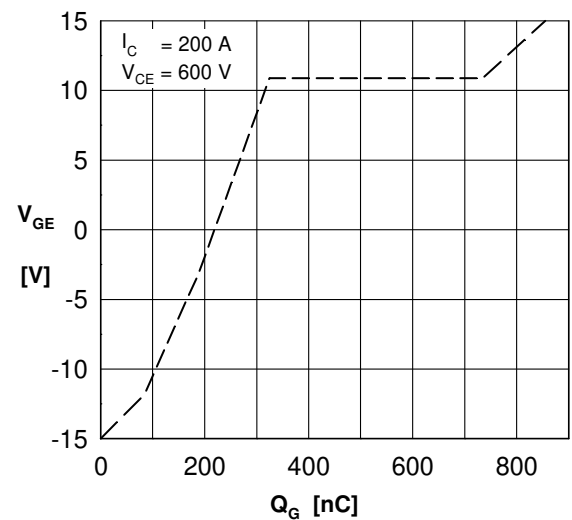


Fig. 6 Typ. turn-on gate charge -15/+15V

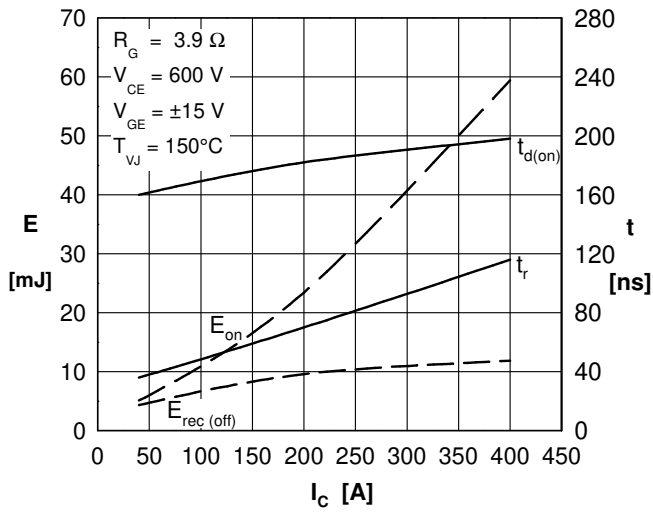
IGBT T1 - T6


Fig. 7 Typ. switching energy versus collector current (turn on)

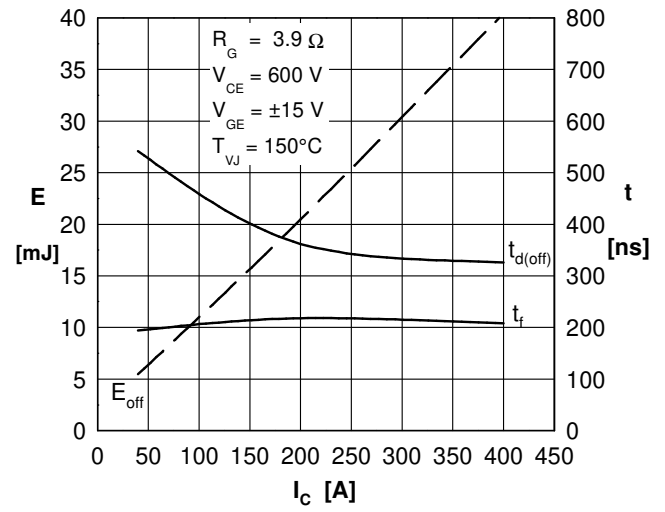


Fig. 8 Typ. switching energy versus collector current (turn off)

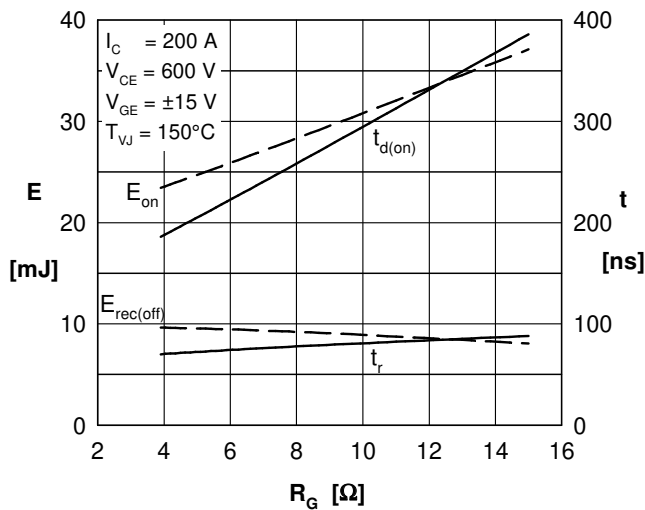


Fig. 9 Typ. switching energy versus gate resistor (turn on)

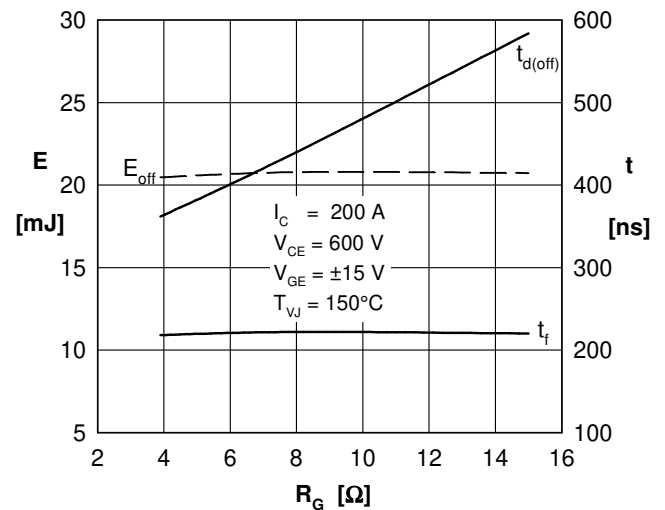


Fig. 10 Typ. switching energy versus gate resistor (turn off)

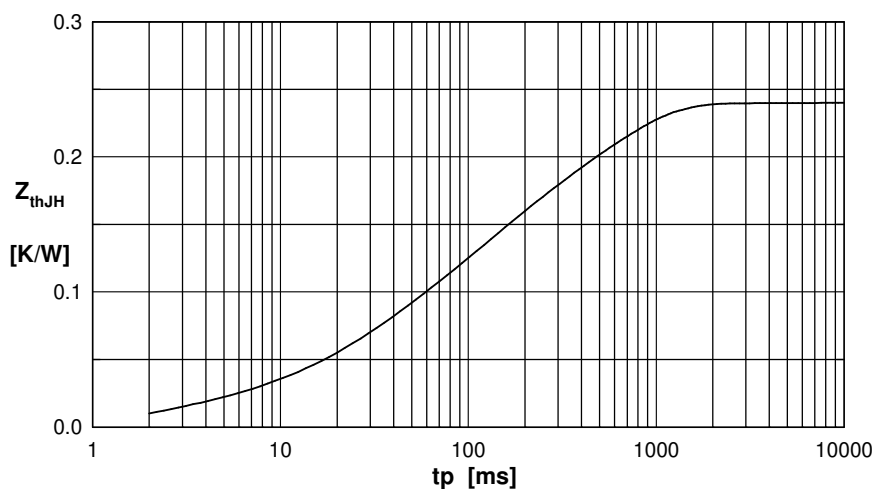


Fig. 11 IGBT: typ. transient thermal impedance to heat sink



DIODE D1 - D6

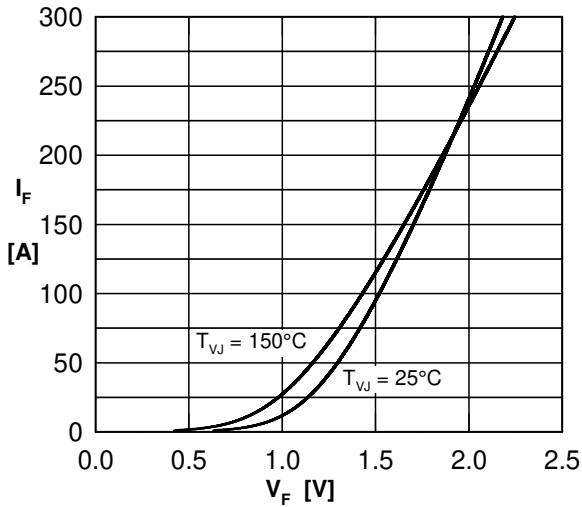


Fig. 12 Typ. forward characteristics FWD

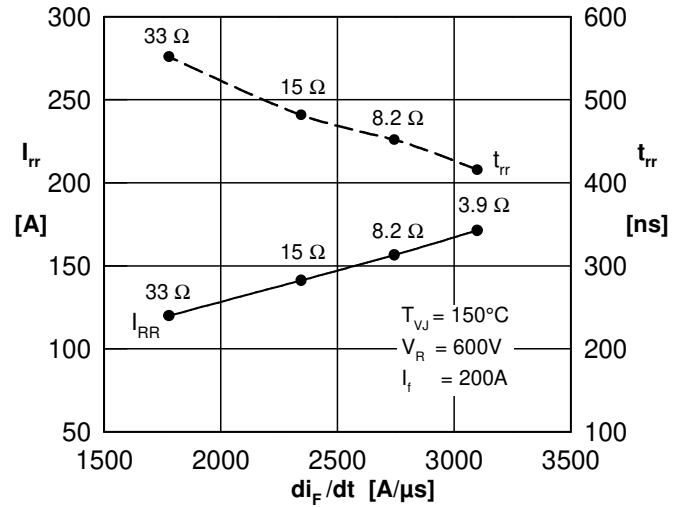


Fig. 13 Typ. recovery energy $E_{rec(off)}$ versus $-di/dt$

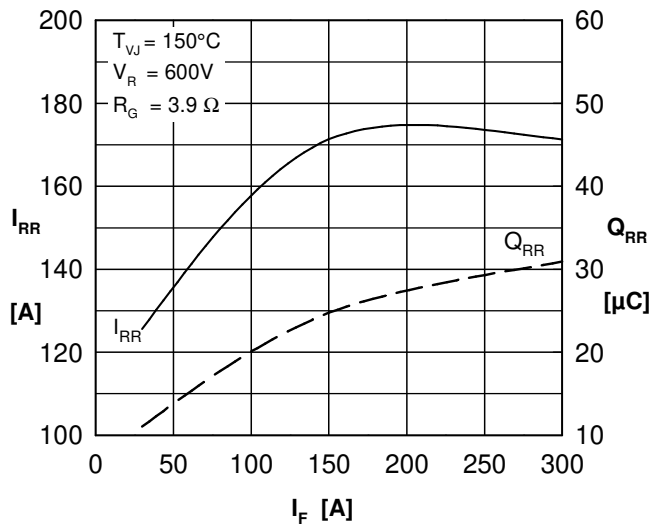


Fig. 14 typ. reverse recovery characteristics

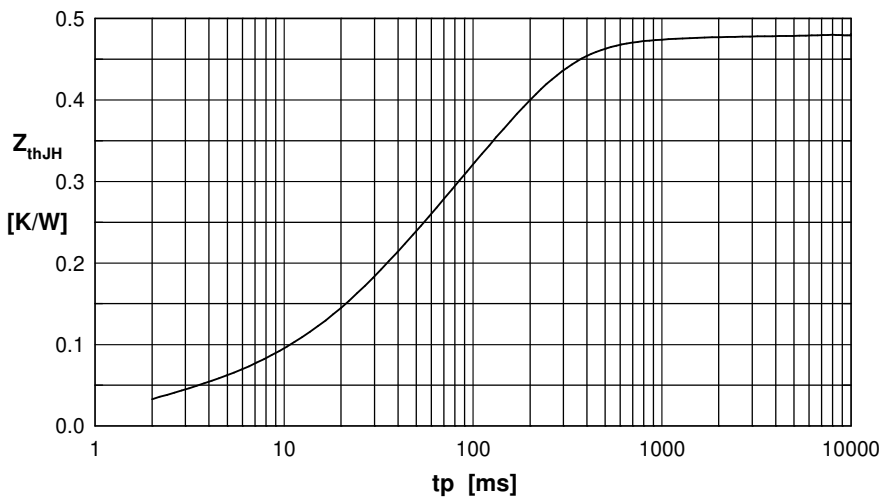


Fig. 15 Diode: typ. transient thermal impedance junction to heat sink